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the sleep mode pins themselves (ZZx) are not affected during sleep mode.

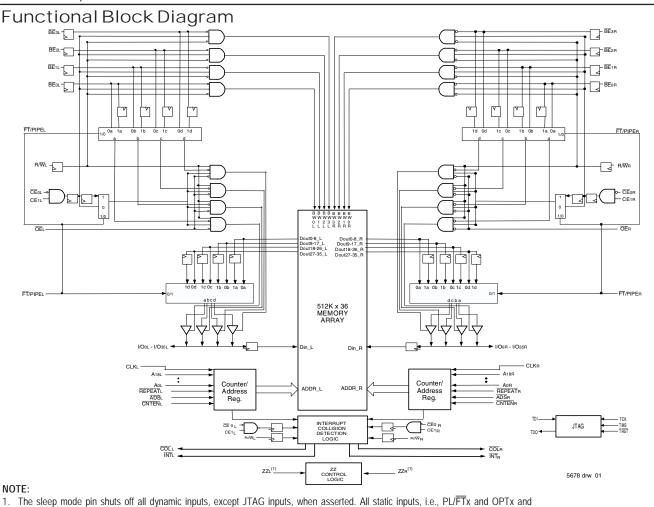
RENESAS

HIGH-SPEED 2.5V 512K x 36 SYNCHRONOUS DUAL-PORT STATIC RAM WITH 3.3V OR 2.5V INTERFACE

Features:

- True Dual-Port memory cells which allow simultaneous access of the same memory location
- High-speed data access
 - Commercial: 3.6ns (166MHz)/4.2ns (133MHz)(max.)
 - Industrial: 4.2ns (133MHz) (max.)
- Selectable Pipelined or Flow-Through output mode
- Counter enable and repeat features
- Dual chip enables allow for depth expansion without additional logic
- Interrupt and Collision Detection Flags
- Full synchronous operation on both ports
 - 6ns cycle time, 166MHz operation (12Gbps bandwidth)
 - Fast 3.6ns clock to data out
 - 1.5ns setup to clock and 0.5ns hold on all control, data, and address inputs @ 166MHz

- Data input, address, byte enable and control registers
 Self-timed write allows fast cycle time
- Separate byte controls for multiplexed bus and bus matching compatibility
- Dual Cycle Deselect (DCD) for Pipelined Output Mode
- 2.5V (±100mV) power supply for core
- LVTTL compatible, selectable 3.3V (±150mV) or 2.5V (±100mV) power supply for I/Os and control signals on each port
- Includes JTAG functionality
- Industrial temperature range (-40°C to +85°C) is available at 133MHz
- Available in a 256-pin Ball Grid Array (BGA)
- Green parts available, see ordering information



JUNE 2019



70T3539M High-Speed 2.5V 512K x 36 Dual-Port Synchronous Static RAM

Description:

The IDT70T3539M is a high-speed 512K x 36 bit synchronous Dual-Port RAM. The memory array utilizes Dual-Port memory cells to allow simultaneous access of any address from both ports. Registers on control, data, and address inputs provide minimal setup and hold times. The timing latitude provided by this approach allows systems to be designed with very short cycle times. With an input data register, the IDT70T3539M has been optimized for applications having unidirectional or bidirectional data flow in bursts. An automatic power down feature, controlled by \overline{CE}_0 and CE1, permits the on-chip circuitry of each port to enter a very low standby power mode.

The 70T3539M can support an operating voltage of either 3.3V or 2.5V on one or both ports, controllable by the OPT pins. The power supply for the core of the device (VDD) is at 2.5V.

70T3539M High-Speed 2.5V 512K x 36 Dual-Port Synchronous Static RAM

5678 drw 02d

Pin Configuration (1,2,3,4)

70T3539M BC256⁽⁵⁾ BCG256⁽⁵⁾

256-Pin BGA Top View⁽⁶⁾

10/07/03

A1	^{A2}	A3	A4	A5	A6	A7	A8	A9	A10	A11	A12	A13	A14	A15	A16
NC	TDI	NC	A17L	A14L	A11L	A8L	BE2L	CE1L	OEL	CNTENL	A 5L	A2L	A0L	NC	NC
B1	^{B2}	^{B3}	B4	B5	B6	B7	B8	B9	^{B10}	b11	B12	B13	B14	в15	^{B16} NC
I/O18L	NC	TDO	A18L	A15L	A12L	A9L	BE3L	CE0L	R/WL	Repeatl	A4L	A1L	Vdd	I/O17L	
C1	C2	C3	C4	C5	C6	C7	C8	C9	C10	C11	C12	С13	C14	C15	C16
I/O18R	I/O19L	Vss	A16L	A13L	A10L	A7L	BE1L	BE0L	CLKL	ADSL	A6L	АзL	OPT∟	I/O17R	I/O16L
D1	D2	d3	d4	d5	d6	d7	d8	d9	d10	d11	d12	D13	D14	D15	D16
I/O20R	I/O19R	I/O20l	PIPE/FTL	Vddql	Vddql	Vddqr	Vddqr	Vddql	Vddql	Vddqr	Vddqr	Vdd	I/O15R	I/O15L	I/O16R
E1	e2	e3	e4	e5	e6	e7	E8	^{E9}	E10	e11	e12	e13	Е14	e15	E16
I/O21R	I/O21L	I/O22L	Vddql	Vdd	Vdd	INTL	Vss	Vss	Vss	Vdd	Vdd	Vddqr	I/O13L	I/O14L	I/O14R
f1	f2	f3	f4	F5	F6	F7	F8	^{F9}	F10	F11	F12	f13	F14	F15	F16
I/O23l	I/O22R	I/O23R	Vddql	Vdd	NC	COLL	Vss	Vss	Vss	Vss	Vdd	Vddqr	I/O12R	I/O13R	I/O12L
G1	G2	G3	g4	G5	G6	G7	G8	G9	G10	G11	G12	g13	G14	G15	G16
I/O24R	I/O24L	I/O25L	Vddqr	Vss	Vss	Vss	Vss	Vss	Vss	Vss	Vss	Vddql	I/O10L	I/O11L	I/O11R
h1	H2	h3	h4	-	H6	^{H7}	H8	H9	H10	H11	H12	h13	h14	H15	h16
I/O26l	I/O25R	I/O26R	Vddqr		Vss	Vss	Vss	Vss	Vss	Vss	Vss	Vddql	I/O9r	IO9∟	I/O10R
J1	j2	j3	j4	J5	J6	J7	_{J8}	^{J9}	J10	J11	J12	j13	J14	j15	J16
I/O27L	I/O28R	I/O27R	Vddql	ZZR	Vss	Vss	Vss	Vss	Vss	Vss	ZZ L	Vddqr	I/O8R	I/O7r	I∕O8L
K1	к2	k3	k4	K5	K6	к7	K8	к9	K10	K11	K12	k13	k14	к15	к16
I/O29R	I/O29L	I/O28L	Vddql	Vss	Vss	Vss	Vss	Vss	Vss	Vss	Vss	Vddqr	I/O6r	I/O6L	I/O7L
l1	l2	l3	l4	l5	L6	L7	L8	L9	L10	L11	L12	l13	l14	l15	l16
I/O30l	I/O31R	I/O30R	Vddqr	Vdd	NC	COLR	Vss	Vss	Vss	Vss	Vdd	Vddql	I/O5l	I/O4r	I/O5r
M1	m2	M3	^{M4}	M5	M6	^{M7}	M8	M9	M10	M11	M12	m13	^{M14}	^{M15}	M16
I/O32R	I/O32L	I/O31L	Vddqr	Vdd	Vdd	INTR	Vss	Vss	Vss	Vdd	Vdd	Vddql	I/O3r	I∕O3∟	I/O4L
n1	N2	n3	N4	^{N5}	N6	n7	n8	^{N9}	N10		n12	N13	N14	N15	n16
I/O33l	I/O34R	I/O33r	PIPE/FTr	Vddqr	Vddqr	Vddql	Vddql	Vddqr	Vddqr		Vddql	Vdd	I/O2L	I/O1R	I/O2r
P1	P2	P3	P4	P5	P6	P7	P8	P9	P10	^{p11}	P12	P13	P14	p15	Р16
I/O35R	I/O34L	TMS	A16R	A13R	A10R	A 7R	BE1R	BE0R	CLKR	ADSr	A 6R	A 3R	I/Ool	I/Oor	I/O1L
r1	R2	^{R3}	R4	R5	R6	R7	R8	R9	^{R10}		R12	R13	^{R14}	^{R15}	R16
I/O35l	NC	TRST	A18R	A15R	A12R	A 9R	BE3R	CEOR	R/Wr		A 4R	A 1R	OPTR	NC	NC
⊤1	T2	T3	T4	T5	т6	T7	t8	^{T9}	T10	t11	T12	T13	T14	T15	T16
NC	TCK	NC	A17R	A14R	А11R	A 8R	BE2R	CE1R	OEr	CNTENR	A 5R	A 2R	Aor	NC	NC

NOTES:

1. All VDD pins must be connected to 2.5V power supply.

2. All VDDO pins must be connected to appropriate power supply: 3.3V if OPT pin for that port is set to VDD (2.5V), and 2.5V if OPT pin for that port is set to Vss (0V).

3. All Vss pins must be connected to ground supply.

4. Package body is approximately 17mm x 17mm x 1.4mm, with 1.0mm ball-pitch.

5. This package code is used to reference the package diagram.

6. This text does not indicate orientation of the actual part-marking.

70T3539M High-Speed 2.5V 512K x 36 Dual-Port Synchronous Static RAM

Pin Names

Left Port	Right Port	Names				
CEOL, CE1L	CEOR, CE1R	Chip Enables (Input) ⁽⁵⁾				
R/WL	R/WR	Read/Write Enable (Input)				
ŌĒL	ŌĒR	Output Enable (Input)				
Aol - A18L	A0R - A18R	Address (Input)				
1/Ool - 1/O35l	1/O0r - 1/O35r	Data Input/Output				
CLKL	CLKR	Clock (Input)				
PL/FTL	PL/FTR	Pipeline/Flow-Through (Input)				
ADSL	ADSR	Address Strobe Enable (Input)				
		Counter Enable (Input)				
REPEATL	REPEATR	Counter Repeat ⁽³⁾				
BEOL - BE3L	BEOR - BE3R	Byte Enables (9-bit bytes) (Input) ⁽⁵⁾				
VDDQL	VDDQR	Power (I/O Bus) (3.3V or 2.5V) ⁽¹⁾ (Input)				
OPTL	OPTR	Option for selecting VDDax ^(1,2) (Input)				
ZZL	ZZR	Sleep Mode pin ⁽⁴⁾ (Input)				
	VDD	Power (2.5V) ⁽¹⁾ (Input)				
	Vss	Ground (0V) (Input)				
	TDI	Test Data Input				
	TDO	Test Data Output				
	ТСК	Test Logic Clock (10MHz) (Input)				
	TMS	Test Mode Select (Input)				
=	TRST	Reset (Initialize TAP Controller) (Input)				
ĪNTL	INT R	Interrupt Flag (Output)				
COLL COLR Collision Alert (Output)						

5678 tbl 01

Industrial and Commercial Temperature Ranges

NOTES:

- 1. VDD, OPTx, and VDDDx must be set to appropriate operating levels prior to applying inputs on the I/Os and controls for that port.
- 2. OPTx selects the operating voltage levels for the I/Os and controls on that port. If OPTx is set to Vob (2.5V), then that port's I/Os and controls will operate at 3.3V levels and Vobox must be supplied at 3.3V. If OPTx is set to Vss (0V), then that port's I/Os and address controls will operate at 2.5V levels and Vobox must be supplied at 2.5V. The OPT pins are independent of one another—both ports can operate at 3.3V levels, both can operate at 2.5V levels, or either can operate at 3.3V with the other at 2.5V.

 When REPEAT x is asserted, the counter will reset to the last valid address loaded via ADSx.

4. The sleep mode pin shuts off all dynamic inputs, except JTAG inputs, when asserted. All static inputs, i.e., PL/FTx and OPTx and the sleep mode pins themselves (ZZx) are not affected during sleep mode. It is recommended that boundry scan not be operated during sleep mode.

 Chip Enables and Byte Enables are double buffered when PL/FT = VIH, i.e., the signals take two cycles to deselect.

70T3539M High-Speed 2.5V 512K x 36 Dual-Port Synchronous Static RAM

Industrial and Commercial Temperature Ranges

Truth Table I—Read/Write and Enable Control (1,2,3,4)

ŌĒ	CLK		CE1	BE 3	BE ₂	BE 1	BE 0	R/W	zz	Byte 3 I/O27-35	Byte 2 I/O18-26	Byte 1 I/O9-17	Byte 0 I/O0-8	MODE
Х	Ŷ	Н	Х	Х	Х	Х	Х	Х	L	High-Z	High-Z	High-Z	High-Z	Deselected–Power Down
Х	Ŷ	Х	L	Х	Х	Х	Х	Х	L	High-Z	High-Z	High-Z	High-Z	Deselected–Power Down
Х	Ŷ	L	Н	Н	Н	Н	Н	Х	L	High-Z	High-Z	High-Z	High-Z	All Bytes Deselected
Х	Ŷ	L	Н	Н	Н	Н	L	L	L	High-Z	High-Z	High-Z	Din	Write to Byte 0 Only
Х	Ŷ	L	Н	Н	Н	L	Н	L	L	High-Z	High-Z	Din	High-Z	Write to Byte 1 Only
Х	Ŷ	L	Н	Н	L	Н	Н	L	L	High-Z	Din	High-Z	High-Z	Write to Byte 2 Only
Х	Ŷ	L	Н	L	Н	Н	Н	L	L	Din	High-Z	High-Z	High-Z	Write to Byte 3 Only
Х	Ŷ	L	Н	Н	Н	L	L	L	L	High-Z	High-Z	Din	Din	Write to Lower 2 Bytes Only
Х	Ŷ	L	Н	L	L	Н	Н	L	L	Din	Din	High-Z	High-Z	Write to Upper 2 bytes Only
Х	Ŷ	L	Н	L	L	L	L	L	L	Din	Din	Din	Din	Write to All Bytes
L	Ŷ	L	Н	Н	Н	Н	L	Н	L	High-Z	High-Z	High-Z	Dout	Read Byte 0 Only
L	Ŷ	L	Н	Н	Н	L	Н	Н	L	High-Z	High-Z	Dout	High-Z	Read Byte 1 Only
L	Ŷ	L	Н	Н	L	Н	Н	Н	L	High-Z	Dout	High-Z	High-Z	Read Byte 2 Only
L	Ŷ	L	Н	L	Н	Н	Н	Н	L	Dout	High-Z	High-Z	High-Z	Read Byte 3 Only
L	Ŷ	L	Н	Н	Н	L	L	Н	L	High-Z	High-Z	Dout	Dout	Read Lower 2 Bytes Only
L	Ŷ	L	Н	L	L	Н	Н	Н	L	Dout	Dout	High-Z	High-Z	Read Upper 2 Bytes Only
L	Ŷ	L	Н	L	L	L	L	Н	L	Dout	Dout	Dout	Dout	Read All Bytes
Н	Ŷ	Х	Х	Х	Х	Х	Х	Х	L	High-Z	High-Z	High-Z	High-Z	Outputs Disabled
Х	Х	Х	Х	Х	Х	Х	Х	Х	Н	High-Z	High-Z	High-Z	High-Z	Sleep Mode

NOTES:

1. $\underline{"H"} = \underline{VIH}, \underline{"L"} = \underline{VIL}, \underline{"X"} = Don't Care.$

2. \overline{ADS} , \overline{CNTEN} , $\overline{REPEAT} = X$.

3. OE and ZZ are asynchronous input signals.

4. It is possible to read or write any combination of bytes during a given access. A few representative samples have been illustrated here.

Truth Table II—Address Counter Control^(1,2)

Address	Previous Internal Address	Internal Address Used	CLK	ADS	CNTEN	REPEAT ⁽⁶⁾	I/O ⁽³⁾	MODE
An	Х	An	\uparrow	L ⁽⁴⁾	х	Н	Dvo (n)	External Address Used
Х	An	An + 1	\uparrow	Н	L ⁽⁵⁾	Н	D⊮o(n+1)	Counter Enabled—Internal Address generation
Х	An + 1	An + 1	Ŷ	Н	Н	Н	D⊮o(n+1)	External Address Blocked—Counter disabled (An + 1 reused)
Х	Х	An	Ŷ	Х	Х	L ⁽⁴⁾	Dvo(n)	Counter Set to last valid ADS load

NOTES:

1. "H" = VIH, "L" = VIL, "X" = Don't Care.

2. Read and write operations are controlled by the appropriate setting of R/W, CE0, CE1, BEn and OE.

3. Outputs configured in flow-through output mode: if outputs are in pipelined mode the data out will be delayed by one cycle.

4. ADS and REPEAT are independent of all other memory control signals including CE0, CE1 and BEn

5. The address counter advances if CNTEN = VIL on the rising edge of CLK, regardless of all other memory control signals including CEo, CE1, BEn.

6. When REPEAT is asserted, the counter will reset to the last valid address loaded via ADS. This value is not set at power-up: a known location should be loaded via ADS during initialization if desired. Any subsequent ADS access during operations will update the REPEAT address location.

5678 tbl 02

5678 tbl 03

Recommended Operating Temperature and Supply Voltage ⁽¹⁾

Grade	Ambient Temperature	GND	Vdd
Commercial	$0^{\circ}C$ to $+70^{\circ}C$	0V	2.5V <u>+</u> 100mV
Industrial	-40°C to +85°C	0V	2.5V <u>+</u> 100mV
NOTEC			5678 tbl 04

NOTES:

1. This is the parameter TA. This is the "instant on" case temperature.

Recommended DC Operating Conditions with VDD0 at 2.5V

Symbol	Parameter	Min.	Тур.	Max.	Unit
Vdd	Core Supply Voltage	2.4	2.5	2.6	V
VDDQ	I/O Supply Voltage ⁽³⁾	2.4	2.5	2.6	V
Vss	Ground	0	0	0	V
Vін	Input High Volltage (Address, Control & Data I/O Inputs) ⁽³⁾	1.7		Vddq + 100mV ⁽²⁾	v
Vih	Input High Voltage - JTAG	1.7		Vdd + 100mV ⁽²⁾	V
Vih	Input High Voltage - ZZ, OPT, PIPE/FT	Vdd - 0.2V		Vdd + 100mV ⁽²⁾	v
Vı∟	Input Low Voltage	-0.3(1)		0.7	V
Vi∟	Input Low Voltage - ZZ, OPT, PIPE/FT	-0.3 ⁽¹⁾		0.2	v

NOTES:

5678 tbl 05a

5678 tbl 05b

- 1. VIL (min.) = -1.0V for pulse width less than tcyc/2 or 5ns, whichever is less.
- 2. VIH (max.) = VDDQ + 1.0V for pulse width less than tcyc/2 or 5ns, whichever is less.

3. To select operation at 2.5V levels on the I/Os and controls of a given port, the OPT pin for that port must be set to $V_{SS}(0V)$, and V_{DDOX} for that port must be supplied as indicated above.

Recommended DC Operating Conditions with VDDO at 3 3V

Symbol	Parameter	Min.	Тур.	Max.	Unit
Vdd	Core Supply Voltage	2.4	2.5	2.6	V
VDDQ	I/O Supply Voltage ⁽³⁾	3.15	3.3	3.45	V
Vss	Ground	0	0	0	V
Vін	Input High Voltage (Address, Control &Data I/O Inputs) ⁽³⁾	2.0		Vddq + 150mV ⁽²⁾	V
VIH	Input High Voltage - JTAG	1.7		VDD + 100mV ⁽²⁾	V
VIH	Input High Voltage - ZZ, OPT, PIPE/FT	Vdd - 0.2V		Vdd + 100mV ⁽²⁾	V
VIL	Input Low Voltage	-0.3 ⁽¹⁾		0.8	V
VIL	Input Low Voltage - ZZ, OPT, PIPE/FT	-0.3 ⁽¹⁾		0.2	v

NOTES:

1. VIL (min.) = -1.0V for pulse width less than tcyc/2, or 5ns, whichever is less.

2. VIH (max.) = VDDQ + 1.0V for pulse width less than tcyc/2 or 5ns, whichever is less.

 To select operation at 3.3V levels on the I/Os and controls of a given port, the OPT pin for that port must be set to VDD (2.5V), and VDDOX for that port must be supplied as indicated above.

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Absolute Maximum Ratings ⁽¹⁾

Symbol	Rating	Commercial & Industrial	Unit
Vterm (Vdd)	Vod Terminal Voltage with Respect to GND	-0.5 to 3.6	V
Vterm ⁽²⁾ (Vddq)	VDDQ Terminal Voltage with Respect to GND	-0.3 to VDDQ + 0.3	V
V _{TERM⁽²⁾ (INPUTS and I/O's)}	Input and I/O Terminal Voltage with Respect to GND	-0.3 to VDDQ + 0.3	V
TBIAS ⁽³⁾	Temperature Under Bias	-55 to +125	٥C
Tstg	Storage Temperature	-65 to +150	٥C
ИЛ	Junction Temperature	+150	٥C
IOUT(For VDDQ = 3.3V)	DC Output Current	50	mA
IOUT(For VDDQ = 2.5V)	DC Output Current	40	mA
NOTEC			5678 tbl 0

NOTES:

- 1. Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.
- 2. This is a steady-state DC parameter that applies after the power supply has reached its nominal operating value. Power sequencing is not necessary; however, the voltage on any Input or I/O pin cannot exceed VDDo during power supply ramp up.
- 3. Ambient Temperature under DC Bias. No AC Conditions. Chip Deselected.

Capacitance⁽¹⁾

(TA = +25°C, F = 1.0MHz) BGA ONLY

Symbol	Parameter	Conditions ⁽²⁾	Max.	Unit
Cin	Input Capacitance	VIN = 0V	15	рF
Cout ⁽³⁾	Output Capacitance	Vout = 0V	10.5	pF
				5678 tbl 07

NOTES:

 These parameters are determined by device characterization, but are not production tested.

2. COUT also references CI/O.

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range (VDD = 2.5V ± 100mV)

			70T35	39MS	
Symbol	Parameter	Test Conditions	Min.	Max.	Unit
Lu	Input Leakage Current ⁽¹⁾	VDDQ = Max., V IN = 0 V to V DDQ		10	μA
lu	JTAG & ZZ Input Leakage Current ^(1,2)	VDD = Max., VIN = OV to VDD		±30	μA
LO	Output Leakage Current ^(1,3)	$\overline{CE}_0 = V_{IH} \text{ or } CE_1 = V_{IL}, V_{OUT} = 0V \text{ to } V_{DDQ}$		10	μA
Vol (3.3V)	Output Low Voltage ⁽¹⁾	IOL = +4mA, $VDDQ = Min$.	_	0.4	V
Voн (3.3V)	Output High Voltage ⁽¹⁾	IOH = -4mA, VDDQ = Min.	2.4	_	V
Vol (2.5V)	Output Low Voltage ⁽¹⁾	IOL = +2mA, $VDDQ = Min$.	_	0.4	V
Vон (2.5V)	Output High Voltage ⁽¹⁾	Ioh = -2mA, VDDQ = Min.	2.0	_	V

NOTES:

1. VDDQ is selectable (3.3V/2.5V) via OPT pins. Refer to p.5 for details.

2. Applicable only for TMS, TDI and TRST inputs.

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3. Outputs tested in tri-state mode.

Industrial and Commercial Temperature Ranges

5678 thl 08

70T3539M High-Speed 2.5V 512K x 36 Dual-Port Synchronous Static RAM

Industrial and Commercial Temperature Ranges

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range $^{(3)}$ (VDD = 2.5V ± 100mV)

						9MS166 Only	Co	9MS133 m'l nd	
Symbol	Parameter	Test Condition	Versio	n	Тур. ⁽⁴⁾	Max.	Typ. ⁽⁴⁾	Мах.	Uni
IDD	Dynamic Operating Current (Both	CEL and CER= VIL, Outputs Disabled,	COM'L	S	640	900	520	740	mA
	Ports Active)	$f = fMAX^{(1)}$	IND	S			520	900	111/-
ISB1 ⁽⁶⁾	Standby Current	$\overline{CE}_{L} = \overline{CE}_{R} = V_{H}$	COM'L	S	350	460	280	380	
(Both Ports - TTL Level Inputs)	$f = f MAX^{(1)}$	IND	S	_	_	280	470	mA	
ISB2 ⁽⁶⁾ Standby Current	\overline{CE} "A" = VIL and \overline{CE} "B" = VIH ⁽⁵⁾	COM'L	S	500	650	400	500	m	
	(One Port - TTL Level Inputs)	Active Port Outputs Disabled, f=fMAX ⁽¹⁾	IND	S	-		400	620	
ISB3	Full Standby Current	Both Ports CEL and	COM'L	S	12	20	12	20	
	(Both Ports - CMOS Level Inputs)	$\overline{\text{CER}} \ge \text{VDDQ} - 0.2\text{V}, \text{ VIN} \ge \text{VDDQ} - 0.2\text{V}$ or VIN $\le 0.2\text{V}, \text{ f} = 0^{(2)}$	IND	S	-	_	12	25	mA
ISB4 ⁽⁶⁾	Full Standby Current (One Port - CMOS	$\overline{CE}^*A^* \leq 0.2V$ and $\overline{CE}^*B^* \geq VDDQ - 0.2V^{(5)}$	COM'L	S	500	650	400	500	
	Level Inputs)	$VIN \ge VDDQ - 0.2V$ or $VIN \le 0.2V$ Active Port, Outputs Disabled, f = fMAX ⁽¹⁾	IND	S	-	_	400	620	mA
lzz	Sleep Mode Current (Both Ports - TTL	ZZL = ZZR = VIH f=fmax ⁽¹⁾	COM'L	S	12	20	12	20	
	(Both Ports - TTL Level Inputs)			S			12	25	m.

NOTES:

1. At f = fmax, address and control lines (except Output Enable) are cycling at the maximum frequency clock cycle of 1/tcvc, using "AC TEST CONDITIONS".

2. f = 0 means no address, clock, or control lines change. Applies only to input at CMOS level standby.

- 3. Port "A" may be either left or right port. Port "B" is the opposite from port "A".
- 4. VDD = 2.5V, TA = 25°C for Typ, and are not production tested. IDD DC(f=0) = 30mA (Typ).
- 5. $\overline{CEx} = VIL$ means $\overline{CEox} = VIL$ and CE1x = VIH $\overline{CEx} = VIH$ means $\overline{CEox} = VIH$ or CE1x = VIH

 $\overline{\text{CE}}x \leq 0.2V$ means $\overline{\text{CE}}\textsc{ox} \leq 0.2V$ and $\text{CE}\textsc{ix} \geq V\textsc{dd}$ - 0.2V

 $\overline{\text{CE}}\text{x} \geq \text{V}\text{DDQ}$ - 0.2V means $\overline{\text{CE}}\text{ox} \geq \text{V}\text{DDQ}$ - 0.2V or CE1x - 0.2V

"X" represents "L" for left port or "R" for right port.

6. ISB1, ISB2 and ISB4 will all reach full standby levels (ISB3) on the appropriate port(s) if ZZL and/or ZZR = VIH.

70T3539M High-Speed 2.5V 512K x 36 Dual-Port Synchronous Static RAM

AC Test Conditions (VDDQ - 3.3V/2.5V)

Input Pulse Levels (Address & Controls)	GND to 3.0V/GND to 2.4V				
Input Pulse Levels (I/Os)	GND to 3.0V/GND to 2.4V				
Input Rise/Fall Times	2ns				
Input Timing Reference Levels	1.5V/1.25V				
Output Reference Levels	1.5V/1.25V				
Output Load	Figure 1				

5678 tbl 10

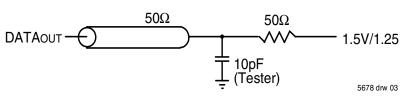
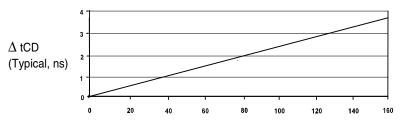


Figure 1. AC Output Test load.



 Δ Capacitance (pF) from AC Test Load 5678 drw 04

Industrial and Commercial Temperature Ranges

70T3539M High-Speed 2.5V 512K x 36 Dual-Port Synchronous Static RAM

Industrial and Commercial Temperature Ranges

AC Electrical Characteristics Over the Operating Temperature Range (Read and Write Cycle Timing) $^{(2,3)}$ (VDD = 2.5V ± 100mV, TA = 0°C to +70°C)

		70T353 Com	39MS166 I Only	70T353 Co &	89MS133 om'l Ind	
Symbol	Parameter	Min.	Max.	Min.	Max.	Unit
tcyc1	Clock Cycle Time (Flow-Through) ⁽¹⁾	20		25		ns
tcyc2	Clock Cycle Time (Pipelined) ⁽¹⁾	6	—	7.5		ns
ICH1	Clock High Time (Flow-Through) ⁽¹⁾	8	—	10		ns
tCL1	Clock Low Time (Flow-Through) ⁽¹⁾	8	—	10		ns
tcн2	Clock High Time (Pipelined) ⁽²⁾	2.4	—	3		ns
tCL2	Clock Low Time (Pipelined) ⁽¹⁾	2.4	—	3		ns
tsa	Address Setup Time	1.7	—	1.8		ns
tha	Address Hold Time	0.5	—	0.5		ns
tsc	Chip Enable Setup Time	1.7		1.8		ns
tнc	Chip Enable Hold Time	0.5		0.5		ns
tsв	Byte Enable Setup Time	1.7		1.8		ns
tнв	Byte Enable Hold Time	0.5	—	0.5		ns
tsw	R/W Setup Time	1.7	—	1.8		ns
tHW	R/W Hold Time	0.5		0.5		ns
tsp	Input Data Setup Time	1.7		1.8		ns
tнD	Input Data Hold Time	0.5		0.5		ns
İSAD	ADS Setup Time	1.7		1.8		ns
thad	ADS Hold Time	0.5		0.5		ns
tscn	CNTEN Setup Time	1.7		1.8		ns
tнсм	CNTEN Hold Time	0.5		0.5		ns
İ SRPT	REPEAT Setup Time	1.7		1.8		ns
thrpt	REPEAT Hold Time	0.5		0.5		ns
toe	Output Enable to Data Valid		4.4		4.6	ns
tolz ⁽⁶⁾	Output Enable to Output Low-Z	1		1		ns
tонz ⁽⁶⁾	Output Enable to Output High-Z	1	3.6	1	4.2	ns
tCD1	Clock to Data Valid (Flow-Through) ⁽¹⁾		12	· · ·	15	ns
tCD2	Clock to Data Valid (Pipelined) ⁽¹⁾		3.6		4.2	ns
tDC	Data Output Hold After Clock High	1		1		ns
tскнz ⁽⁶⁾	Clock High to Output High-Z	1	3.6	1	4.2	ns
tcklz ⁽⁶⁾	Clock High to Output Low-Z	1		1		ns
tins	Interrupt Flag Set Time		7		7	ns
ting	Interrupt Flag Reset Time		7		7	ns
tcols	Collision Flag Set Time		3.6		4.2	ns
tcolr	Collision Flag Reset Time		3.6		4.2	ns
tzzsc	Sleep Mode Set Cycles	2		2	4.Z	cycles
tzzrc	Sleep Mode Recovery Cycles	3		3		cycles
Port-to-Port		5	1			Cycles
	Clock-to-Clock Offset	5		6		ns
		3		U U		115

1. The Pipelined output parameters (tcvc2, tcb2) apply to either or both left and right ports when FT/PIPEx = Vbb (2.5V). Flow-through parameters (tcvc1, tcb1) apply when $\overline{FT}/PIPE = V_{ss}$ (0V) for that port.

2. All input signals are synchronous with respect to the clock except for the asynchronous Output Enable (OE), FT/PIPE and OPT. FT/PIPE and OPT should be treated as DC signals, i.e. steady state during operation.

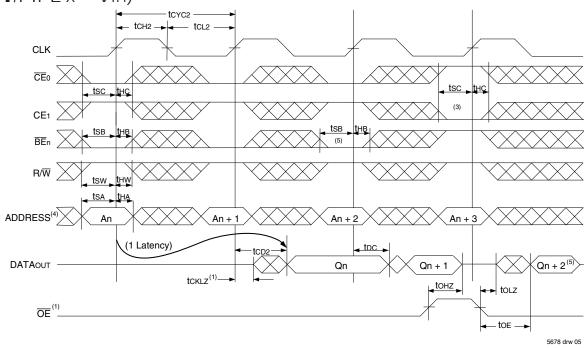
3. These values are valid for either level of VDDQ (3.3V/2.5V). See page 6 for details on selecting the desired operating voltage levels for each port.

4. Guaranteed by design (not production tested).

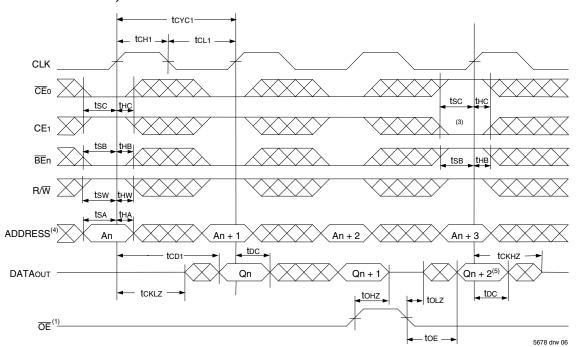
70T3539M High-Speed 2.5V 512K x 36 Dual-Port Synchronous Static RAM

Industrial and Commercial Temperature Ranges



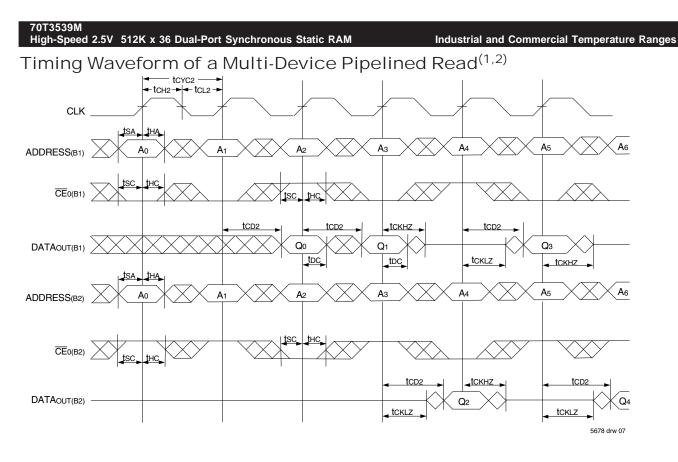


Timing Waveform of Read Cycle for Flow-through Output $(FT/PIPE"x" = VIL)^{(1,2,6)}$

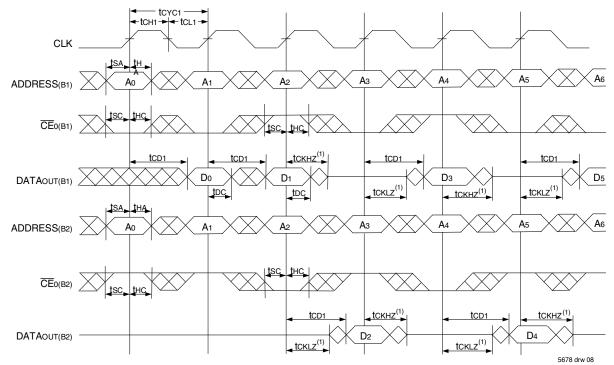


NOTES:

- 1. OE is asynchronously controlled; all other inputs depicted in the above waveforms are synchronous to the rising clock edge.
- 2. $\overline{ADS} = VIL$, \overline{CNTEN} and $\overline{REPEAT} = VIH$.
- 3. The output is disabled (High-Impedance state) by $\overline{CE}_0 = VIH$, $CE_1 = VIL$, $\overline{BE}_n = VIH$ following the next rising edge of the clock. Refer to Truth Table 1.
- Addresses do not have to be accessed sequentially since ADS = ViL constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 5. If BEn was HIGH, then the appropriate Byte of DATAOUT for Qn + 2 would be disabled (High-Impedance state).
- 6. "x" denotes Left or Right port. The diagram is with respect to that port.



Timing Waveform of a Multi-Device Flow-Through Read^(1,2)

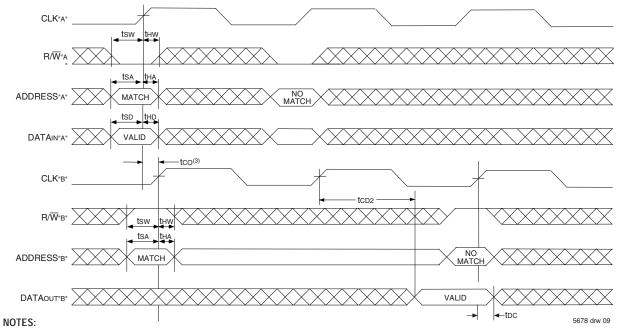


NOTES:

- 1. B1 Represents Device #1; B2 Represents Device #2. Each Device consists of one IDT70T3539M for this waveform,
- and are setup for depth expansion in this example. ADDRESS(B1) = ADDRESS(B2) in this situation.
- 2. $\overline{\text{BE}}n$, $\overline{\text{OE}}$, and $\overline{\text{ADS}} = \text{VIL}$; $\overline{\text{CE1(B1)}}$, $\overline{\text{CE1(B2)}}$, $\overline{\text{R/W}}$, $\overline{\text{CNTEN}}$, and $\overline{\text{REPEAT}} = \text{VIH}$.

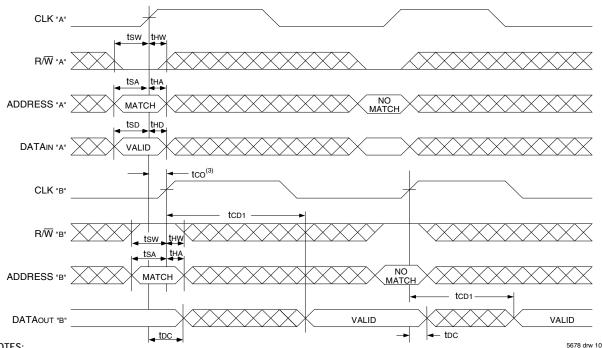
70T3539M High-Speed 2.5V 512K x 36 Dual-Port Synchronous Static RAM

Timing Waveform of Left Port Write to Pipelined Right Port Read^(1,2,4)



- 1. \overline{CE}_0 , \overline{BE}_n , and $\overline{ADS} = VIL$; CE1, \overline{CNTEN} , and $\overline{REPEAT} = VIH$.
- 2. $\overline{OE} = V_{IL}$ for Port "B", which is being read from. $\overline{OE} = V_{IH}$ for Port "A", which is being written to.
- 3. If tco ≤ minimum specified, then data from Port "B" read is not valid until following Port "B" clock cycle (ie, time from write to valid read on opposite port will be tco + 2 tcyc2 + tcp2). If tco > minimum, then data from Port "B" read is available on first Port "B" clock cycle (ie, time from write to valid read on opposite port will be tco + tcyc2 + tcp2).
- 4. All timing is the same for Left and Right ports. Port "A" may be either Left or Right port. Port "B" is the opposite of Port "A"

Timing Waveform with Port-to-Port Flow-Through Read^(1,2,4)



NOTES:

1. \overline{CE}_{0} , \overline{BE}_{n} , and $\overline{ADS} = V_{IL}$; CE_{1} , \overline{CNTEN} , and $\overline{REPEAT} = V_{IH}$.

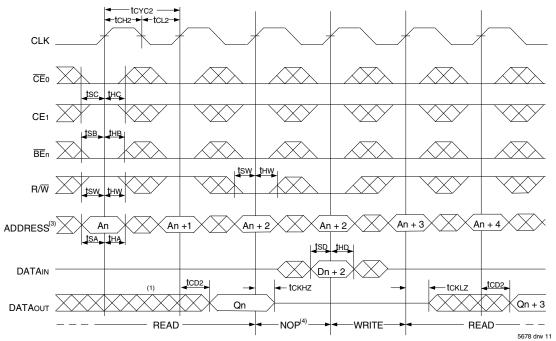
2. $\overline{OE} = V_{IL}$ for the Right Port, which is being read from. $\overline{OE} = V_{IH}$ for the Left Port, which is being written to.

- If tco ≤ minimum specified, then data from Port "B" read is not valid until following Port "B" clock cycle (i.e., time from write to valid read on opposite port will be tco + tcyc + tcp1). If tco > minimum, then data from Port "B" read is available on first Port "B" clock cycle (i.e., time from write to valid read on opposite port will be tco + tcp1).
- 4. All timing is the same for both left and right ports. Port "A" may be either left or right port. Port "B" is the opposite of Port "A".

70T3539M High-Speed 2.5V 512K x 36 Dual-Port Synchronous Static RAM

Industrial and Commercial Temperature Ranges

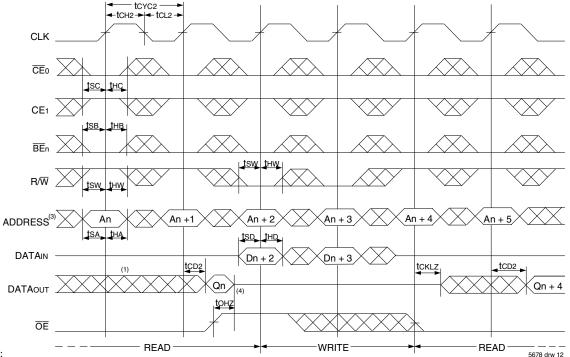
Timing Waveform of Pipelined Read-to-Write-to-Read ($\overline{OE} = VIL$)⁽²⁾



NOTES:

- 1. Output state (High, Low, or High-impedance) is determined by the previous cycle control signals. 2. $\overline{CE_0}$, $\overline{BE_n}$, and $\overline{ADS} = V_{IL}$; CE_1 , \overline{CNTEN} , and $\overline{REPEAT} = V_{IH}$. "NOP" is "No Operation".
- Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers 3. are for reference use only.
- 4. "NOP" is "No Operation." Data in memory at the selected address may be corrupted and should be re-written to guarantee data integrity.

Timing Waveform of Pipelined Read-to-Write-to-Read (**OE** Controlled)⁽²⁾



NOTES:

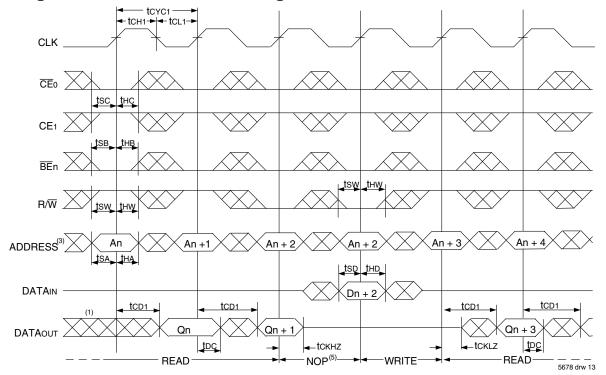
1. Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.

- 2. TEO, BEn, and ADS = VIL; CE1, CNTEN, and REPEAT = VIH.
- Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers are for reference 3. use only.
- 4. This timing does not meet requirements for fastest speed grade. This waveform indicates how logically it could be done if timing so allows.

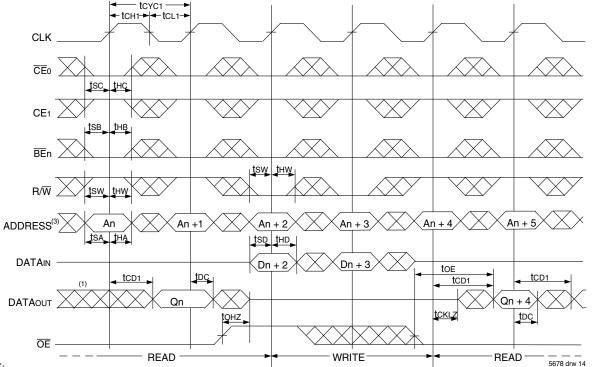
70T3539M High-Speed 2.5V 512K x 36 Dual-Port Synchronous Static RAM

Industrial and Commercial Temperature Ranges

Timing Waveform of Flow-Through Read-to-Write-to-Read ($\overline{OE} = VIL$)⁽²⁾



Timing Waveform of Flow-Through Read-to-Write-to-Read (**OE** Controlled)⁽²⁾



NOTES:

1. Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.

2. TEO, BEn, and ADS = VIL; CE1, CNTEN, and REPEAT = VIH.

3. Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers are for reference use only.

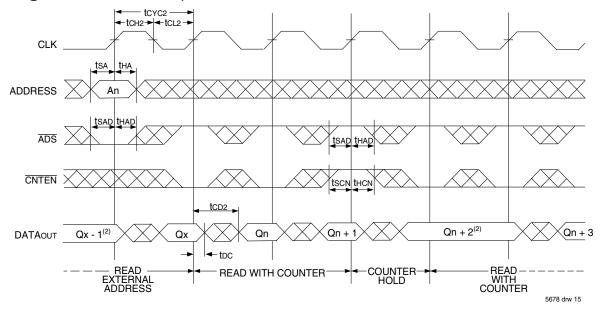
4. "NOP" is "No Operation." Data in memory at the selected address may be corrupted and should be re-written to guarantee data integrity.



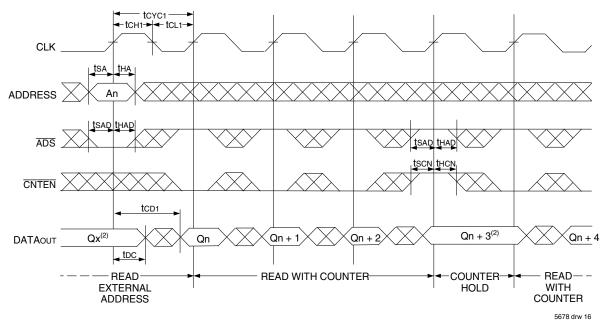
70T3539M High-Speed 2.5V 512K x 36 Dual-Port Synchronous Static RAM

Industrial and Commercial Temperature Ranges

Timing Waveform of Pipelined Read with Address Counter Advance⁽¹⁾



Timing Waveform of Flow-Through Read with Address Counter Advance⁽¹⁾



NOTES:

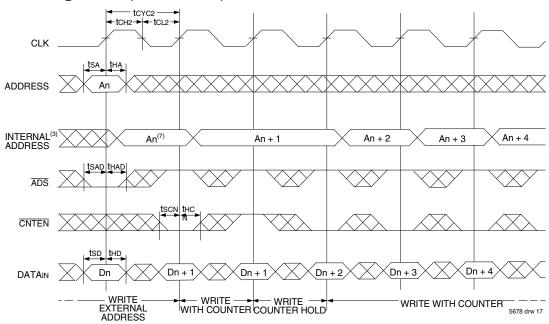
1. \overline{CE}_{0} , \overline{OE} , \overline{BE}_{n} = VIL; CE1, R/W, and \overline{REPEAT} = VIH.

2. If there is no address change via $\overline{ADS} = V_{IL}$ (loading a new address) or $\overline{CNTEN} = V_{IL}$ (advancing the address), i.e. $\overline{ADS} = V_{IH}$ and $\overline{CNTEN} = V_{IH}$, then the data output remains constant for subsequent clocks.

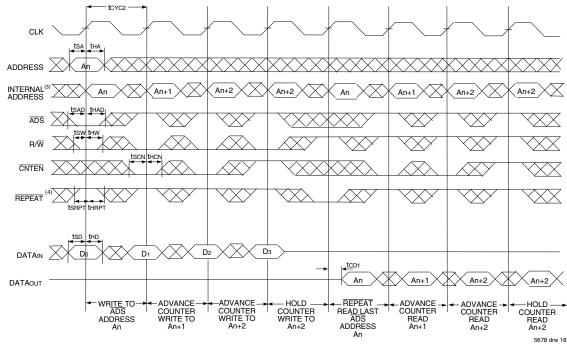
70T3539M High-Speed 2.5V 512K x 36 Dual-Port Synchronous Static RAM

Industrial and Commercial Temperature Ranges

Timing Waveform of Write with Address Counter Advance (Flow-through or Pipelined Inputs)⁽¹⁾



Timing Waveform of Counter Repeat^(2,6)

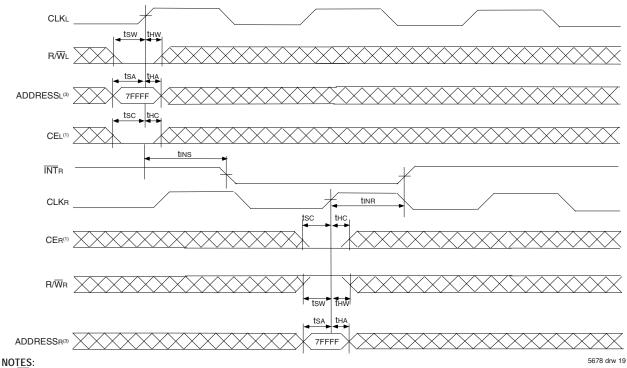


- NOTES:
- 1. \overline{CE}_0 , \overline{BE}_n , and $R/\overline{W} = VIL$; CE1 and $\overline{REPEAT} = VIH$. 2. \overline{CE}_{0} , \overline{BE}_{n} = VIL; CE1 = VIH.
- 3. The "Internal Address" is equal to the "External Address" when \overline{ADS} = VIL and equals the counter output when \overline{ADS} = VIH.
- No dead cycle exists during REPEAT operation. A READ or WRITE cycle may be coincidental with the counter REPEAT cycle: Address loaded by last valid 4. ADS load will be accessed. For more information on REPEAT function refer to Truth Table II.
- 5. CNTEN = VIL advances Internal Address from 'An' to 'An +1'. The transition shown indicates the time required for the counter to advance. The 'An +1'Address is written to during this cycle.
- 6. For Pipelined Mode user should add 1 cycle latency for outputs as per timing waveform of read cycle for pipelined operations.

70T3539M High-Speed 2.5V 512K x 36 Dual-Port Synchronous Static RAM

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Waveform of Interrupt Timing⁽²⁾



1. $\overline{CE}_0 = VIL \text{ and } CE_1 = VIH$

- All timing is the same for Left and Right ports.
- 3. Address is for internal register, not the external bus, i.e., address needs to be qualified by one of the Address counter control signals.

		Left Port					Right Port			
CLKL	R/₩ L ⁽²⁾	CEL ⁽²⁾	A18L-A0L	ĪNTL	CLKr	R/ W R ⁽²⁾	CER ⁽²⁾	A18R-A0R	ĪNTR	Function
↑	L	L	7FFFF	Х	Ŷ	Х	Х	Х	L	Set Right INTR Flag
Ŷ	Х	х	Х	Х	Ŷ	Н	L	7FFFF	Н	Reset Right INTR Flag
Ŷ	Х	Х	Х	L	Ŷ	L	L	7FFFE	Х	Set Left INTL Flag
Ŷ	Н	L	7FFFE	Н	Ŷ	Х	Х	Х	Х	Reset Left INTL Flag

Truth Table III — Interrupt Flag⁽¹⁾

NOTES:

1. INTL and INTR must be initialized at power-up by Resetting the flags.

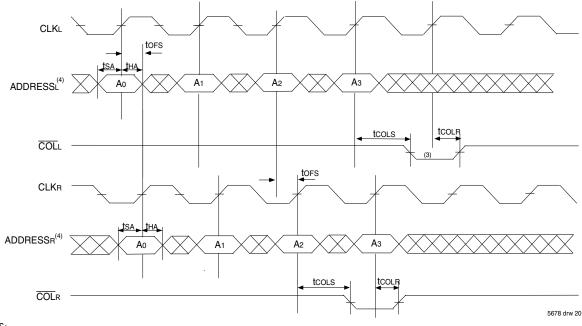
2. CE0 = VIL and CE1 = VIH. R/W and CE are synchronous with respect to the clock and need valid set-up and hold times.

3. Address is for internal register, not the external bus, i.e., address needs to be qualified by one of the Address counter control signals.

70T3539M High-Speed 2.5V 512K x 36 Dual-Port Synchronous Static RAM

Industrial and Commercial Temperature Ranges

Waveform of Collision Timing^(1,2)



NOTES:

1. $\overline{CE}_0 = V_{IL}, CE_1 = V_{IH}.$

2. For reading port, OE is a Don't care on the Collision Detection Logic. Please refer to Truth Table IV for specific cases.

3. Leading Port Output flag might output 3tcyc2 + tcoLs after Address match.

4. Address is for internal register, not the external bus, i.e., address needs to be qualified by one of the Address counter control signals.

Collision Detection Timing^(3,4)

Cuelo Timo	tofs (ns)			
Cycle Time	Region 1 (ns) ⁽¹⁾	Region 2 (ns) ⁽²⁾		
5ns	0 - 2.8	2.81 - 4.6		
6ns	0 - 3.8	3.81 - 5.6		
7.5ns	0 - 5.3	5.31 - 7.1		

NOTES:

- 1. Region 1
- Both ports show collision after 2nd cycle for Addresses 0, 2, 4 etc. 2. Region 2

Leading port shows collision after 3rd cycle for addresses 0, 3, 6, etc. while trailing port shows collision after 2nd cycle for addresses 0, 2, 4 etc.

5678 tbl 14

- 3. All the production units are tested to midpoint of each region.
- 4. These ranges are based on characterization of a typical device.

Truth Table IV — Collision Detection Flag

	Left Port					Right Port				
CLKL	R/WL ⁽¹⁾	CEL ⁽¹⁾	A18L-A0L ⁽²⁾	COLL	CLKr	R/ W R ⁽¹⁾	CER ⁽¹⁾	A18R-A0R ⁽²⁾	COLR	Function
¢	Н	L	MATCH	Н	Ŷ	Н	L	MATCH	Н	Both ports reading. Not a valid collision. No flag output on either port.
¢	Н	L	MATCH	L	Ŷ	L	L	MATCH	Н	Left port reading, Right port writing. Valid collision, flag output on Left port.
¢	L	L	MATCH	Н	Ŷ	Н	L	MATCH	L	Right port reading, Left port writing. Valid collision, flag output on Right port.
¢	L	L	MATCH	L	Ŷ	L	L	MATCH	L	Both ports writing. Valid collision. Flag output on both ports.

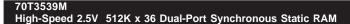
NOTES:

1. $\overline{CE_0} = V_{IL}$ and $CE_1 = V_{IH}$. R/\overline{W} and CE are synchronous with respect to the clock and need valid set-up and hold times.

2. Address is for internal register, not the external bus, i.e., address needs to be qualified by one of the Address counter control signals.

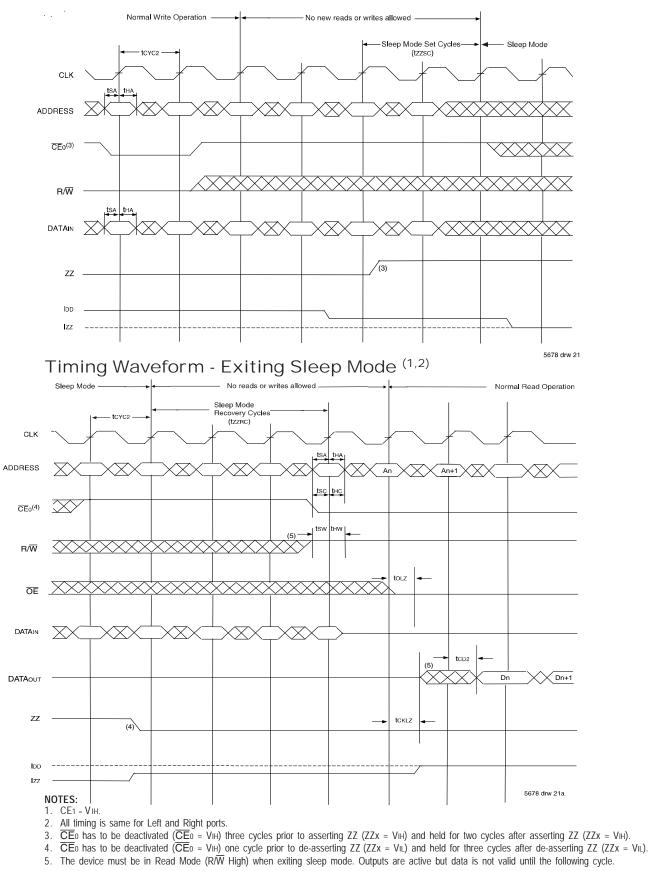
⁵⁶⁷⁸ tbl 13





Industrial and Commercial Temperature Ranges

Timing Waveform - Entering Sleep Mode (1,2)



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70T3539M High-Speed 2.5V 512K x 36 Dual-Port Synchronous Static RAM

Functional Description

The IDT70T3539M provides a true synchronous Dual-Port Static RAM interface. Registered inputs provide minimal set-up and hold times on address, data, and all critical control inputs. All internal registers are clocked on the rising edge of the clock signal, however, the self-timed internal write pulse width is independent of the cycle time.

An asynchronous output enable is provided to ease asynchronous bus interfacing. Counter enable inputs are also provided to stall the operation of the address counters for fast interleaved memory applications.

A HIGH on \overline{CE} or a LOW on CE1 for one clock cycle will power down the internal circuitry to reduce static power consumption. Multiple chip enables allow easier banking of multiple IDT70T3539Ms for depth expansion configurations. Two cycles are required with \overline{CE} LOW and CE1 HIGH to re-activate the outputs.

Interrupts

If the user chooses the interrupt function, a memory location (mail box or message center) is assigned to each port. The left port interrupt flag (\overline{INTL}) is asserted when the right port writes to memory location 7FFFE (HEX), where a write is defined as $\overline{CER} = R/\overline{WR} = VIL$ per the Truth Table. The left port clears the interrupt through access of address location 7FFFE when $\overline{CEL} = VIL$ and $R/\overline{WL} = VIH$. Likewise, the right port interrupt flag (\overline{INTR}) is asserted when the left port writes to memory location 7FFFF (HEX) and to clear the interrupt flag (\overline{INTR}), the right port must read the memory location 7FFFF. The message (36 bits) at 7FFFE or 7FFFF is user-defined since it is an addressable SRAMIocation. If the interrupt function is not used, address locations 7FFFE and 7FFFF are not used as mail boxes, but as part of the random access memory. Refer to Truth Table III for the interrupt operation.

Collision Detection

Collision is defined as an overlap in access between the two ports resulting in the potential for either reading or writing incorrect data to a specific address. For the specific cases: (a) Both ports reading - no data is corrupted, lost, or incorrectly output, so no collision flag is output on either port. (b) One port writing, the other port reading port might capture data that is in a state of transition and hence the reading port's collision flag is output. (c) Both ports writing - there is a risk that the two ports will interfere with each other, and the data stored in memory will not be a valid write from either port (it may essentially be a random combination of the two). Therefore, the collision flag is output on both ports. Please refer to Truth Table IV for all of the above cases.

The alert flag (\overline{COL}_x) is asserted on the 2nd or 3rd rising clock edge of the affected port following the collision, and remains low for one cycle. Please refer to Collision Detection Timing Table on Page 19. During that next cycle, the internal arbitration is engaged in resetting the alert flag (this avoids a specific requirement on the part of the user to reset the alert flag). If two collisions occur on subsequent clock cycles, the second collision may not generate the appropriate alert flag. A third collision will generate the alert flag as appropriate. In the event that a user initiates a burst access on both ports with the same starting address on both ports and one or both ports writing during each access (i.e., imposes a long string of collisions on contiguous clock cycles), the alert flag will be asserted and cleared every other cycle. Please refer to the Collision Detection timing waveform on Page 19.

Collision detection on the IDT70T3539M represents a significant advance in functionality over current sync multi-ports, which have no such capability. In addition to this functionality the IDT70T3539M sustains the key features of bandwidth and flexibility. The collision detection function is very useful in the case of bursting data, or a string of accesses made to sequential addresses, in that it indicates a problem within the burst, giving the user the option of either repeating the burst or continuing to watch the alert flag to see whether the number of collisions increases above an acceptable threshold value. Offering this function on chip also allows users to reduce their need for arbitration circuits, typically done in CPLD's or FPGA's. This reduces board space and design complexity, and gives the user more flexibility in developing a solution.

Sleep Mode

The IDT70T3539M is equipped with an optional sleep or low power mode on both ports. The sleep mode pin on both ports is asynchronous and active high. During normal operation, the ZZ pin is pulled low. When ZZ is pulled high, the port will enter sleep mode where it will meet lowest possible power conditions. The sleep mode timing diagram shows the modes of operation: Normal Operation, No Read/Write Allowed and Sleep Mode.

For normal operation all inputs must meet setup and hold times prior to sleep and after recovering from sleep. Clocks must also meet cycle high and low times during these periods. Three cycles prior to asserting ZZ (ZZx = VIH) and three cycles after de-asserting ZZ (ZZx = VIL), the device must be disabled via the chip enable pins. If a write or read operation occurs during these periods, the memory array may be corrupted. Validity of data out from the RAM cannot be guaranteed immediately after ZZ is asserted (prior to being in sleep). When exiting sleep mode, the device must be in Read mode (R/Wx = VIH) when chip enable is asserted, and the chip enable must be valid for one full cycle before a read will result in the output of valid data.

During sleep mode the RAM automatically deselects itself. The RAM disconnects its internal clock buffer. The external clock may continue to run without impacting the RAMs sleep current (Izz). All outputs will remain in high-Z state while in sleep mode. All inputs are allowed to toggle. The RAM will not be selected and will not perform any reads or writes.

Industrial and Commercial Temperature Ranges

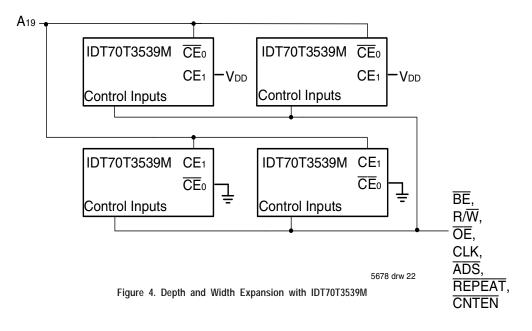
70T3539M High-Speed 2.5V 512K x 36 Dual-Port Synchronous Static RAM

Industrial and Commercial Temperature Ranges

Depth and Width Expansion

The IDT70T3539M features dual chip enables (refer to Truth Table I) in order to facilitate rapid and simple depth expansion with no requirements for external logic. Figure 4 illustrates how to control the various chip enables in order to expand two devices in depth.

The IDT70T3539M can also be used in applications requiring expanded width, as indicated in Figure 4. Through combining the control signals, the devices can be grouped as necessary to accommodate applications needing 72-bits or wider.



JTAG Functionality and Configuration

The IDT70T3539M is composed of two independent memory arrays, and thus cannot be treated as a single JTAG device in the scan chain. The two arrays (A and B) each have identical characteristics and commands but must be treated as separate entities in JTAG operations. Please refer to Figure 5.

JTAG signaling must be provided serially to each array and utilize the information provided in the Identification Register Definitions, Scan

Register Sizes, and System Interface Parameter tables. Specifically, commands for Array B must precede those for Array A in any JTAG operations sent to the IDT70T3539M. Please reference Application Note AN-411, "JTAG Testing of Multichip Modules" for specific instructions on performing JTAG testing on the IDT70T3539M. AN-411 is available at www.idt.com.

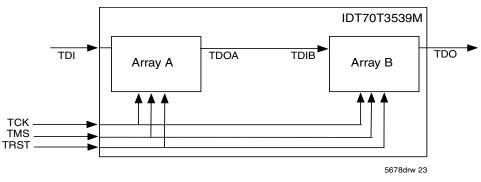
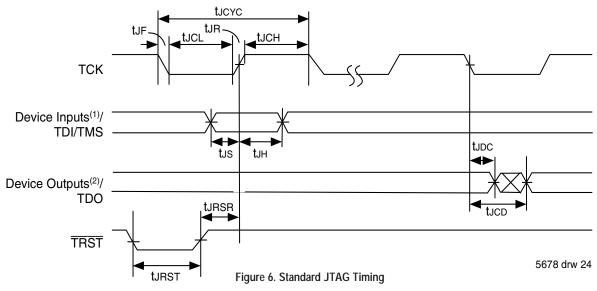


Figure 5. JTAG Configuration for IDT70T3539M

70T3539M High-Speed 2.5V 512K x 36 Dual-Port Synchronous Static RAM

Industrial and Commercial Temperature Ranges

JTAG Timing Specifications



NOTES:

1. Device inputs = All device inputs except TDI, TMS, and TRST.

2. Device outputs = All device outputs except TDO.

		70T3539M		
Symbol	Parameter	Min.	Max.	Units
ticyc	JTAG Clock Input Period	100	-	ns
tлсн	JTAG Clock HIGH	40		ns
ticl	JTAG Clock Low	40	_	ns
tur	JTAG Clock Rise Time		3(1)	ns
tJF	JTAG Clock Fall Time		3(1)	ns
URST	JTAG Reset	50		ns
URSR	JTAG Reset Recovery	50	_	ns
ticd	JTAG Data Output		25	ns
tudo	JTAG Data Output Hold	0		ns
tıs	JTAG Setup	15		ns
tн	JTAG Hold	15		ns

JTAG AC Electrical Characteristics^(1,2,3,4)

NOTES:

1. Guaranteed by design.

2. 30pF loading on external output signals.

3. Refer to AC Electrical Test Conditions stated earlier in this document.

4. JTAG operations occur at one speed (10MHz). The base device may run at any speed specified in this datasheet.

5678 tbl 15

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Identification Register Definitions

Instruction Field Array B	Value Array B	Instruction Field Array A	Value Array A	Description
Revision Number (31:28)	0x0	Revision Number (63:60)	0x0	Reserved for Version number
IDT Device ID (27:12)	0x333	IDT Device ID (59:44)	0x333	Defines IDT Part number
IDT JEDEC ID (11:1)	0x33	IDT JEDEC ID (43:33)	0x33	Allows unique identification of device vendor as IDT
ID Register Indicator Bit (Bit 0)	1	ID Register Indicator Bit (Bit 32)	1	Indicates the presence of an ID Register

5678 tbl 16

Scan Register Sizes

Register Name	Bit Size Array A	Bit Size Array B	Bit Size 70T3539M
Instruction (IR)	4	4	8
Bypass (BYR)	1	1	2
Identification (IDR)	32	32	64
Boundary Scan (BSR)	Note (3)	Note (3)	Note (3)
			E(30 th) 17

5678 tbl 17

System Interface Parameters

Instruction	Code	Description		
EXTEST	00000000	Forces contents of the boundary scan cells onto the device outputs ⁽¹⁾ . Places the boundary scan register (BSR) between TDI and TDO.		
BYPASS	11111111	Places the bypass register (BYR) between TDI and TDO.		
IDCODE	00100010	Loads the ID register (IDR) with the vendor ID code and places the register between TDI and TDO.		
HIGHZ	01000100	Places the bypass register (BYR) between TDI and TDO. Forces all device output drivers except \overline{INTx} and \overline{COLx} to a High-Z state.		
CLAMP	00110011	Uses BYR. Forces contents of the boundary scan cells onto the devioutputs. Places the bypass register (BYR) between TDI and TDO.		
SAMPLE/PRELOAD	00010001 Places the boundary scan register (BSR) between TDI and TDO. SAMPLE allows data from device inputs ⁽²⁾ to be captured in the boundary scan cells and shifted serially through TDO. PRELOAD allows data to be input serially into the boundary scan cells via the TDI.			
RESERVED	01010101, 01110111, 10001000, 10011001, 10101010, 10111011, 11001100	Several combinations are reserved. Do not use codes other than those identified above.		
PRIVATE 01100110,11101110, 1101110, 1101110, 1101110, 1101110, 1101110, 11011101		For internal use only.		

5678 tbl 18

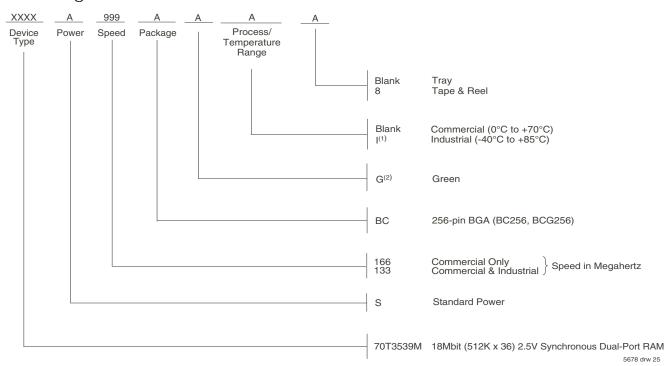
NOTES:

- 1. Device outputs = All device outputs except TDO.
- 2. Device inputs = All device inputs except TDI, TMS, and $\overline{\text{TRST}}$.
- 3. The Boundary Scan Descriptive Language (BSDL) file for this device is available on the IDT website (www.idt.com), or by contacting your local IDT sales representative.

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Industrial and Commercial Temperature Ranges

Ordering Information



NOTES:

 $1. \ Contact \ your \ local \ sales \ office \ for \ industrial \ temp \ range \ for \ other \ speeds, \ packages \ and \ powers.$

 $2.\,Green\,parts\,available.\,For\,specific\,speeds, packages\,and\,powers\,contact\,your\,sales\,office.$

Orderable Part Information

Speed (ns)	Orderable Part ID	Pkg. Code	Pkg. Type	Temp. Grade
133	70T3539MS133BC	BC256	CABGA	С
	70T3539MS133BC8	BC256	CABGA	С
	70T3539MS133BCG	BCG256	CABGA	С
	70T3539MS133BCGI	BCG256	CABGA	1
	70T3539MS133BCI	BC256	CABGA	1
	70T3539MS133BCl8	BC256	CABGA	1
166	70T3539MS166BC	BC256	CABGA	С
	70T3539MS166BC8	BC256	CABGA	С
	70T3539MS166BCG	BCG256	CABGA	С

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Datasheet Document History:

Datasheet
1 Added "Includes JTAG functionality" to features
25 Added IDT Clock Solution Table
10 Added tors symbol and parameter to AC Electrical Characteristics table
19 Updated Collision Timing waveform
19 Added Collision Detection Timing table and footnotes
22 Added JTAG Configuration and JTAG Functionality descriptions
8 Changed IsB3 and Izz in the DC Electrical Characteristics table
20 & 21 Clarified Sleep Mode Text and Waveform
22 Added an Application Note, AN-411, reference to the JTAG Functionality and Configuration text
4 Added another sentence to footnote 4 to recommend that boundary scan not be operated during sleep mode
ved "Preliminary" status
8 Corrected a typo in the footnotes of the DC Chars table
25 Removed "IDT" from orderable part number
7 Corrected the Capacitance Table Title
1 Added Green parts availability to features
26 Added Tape and Reel and Green indicators with their footnote annotations to the Ordering Information
ct Discontinuation Notice - PDN# SP-17-02
me buy expires June 15, 2018
ved erroneous note PDN#SP-17-02
3 & 25 The package code BC-256 changed to BC256 and BCG256 to match standard package code
25 Removed IDT Clock Solutions table
25 Added Orderable Part Information

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